



# BUK9M20-40H

N-channel 40 V, 20.0 mΩ logic level MOSFET in LPAK33

29 January 2019

Product data sheet

## 1. General description

Automotive qualified logic level N-channel MOSFET in an LPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
  - Low power losses, high power density
- LPAK copper clip package technology:
  - High robustness and reliability
  - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

## 3. Applications

- 12 V automotive systems
- Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

## 4. Quick reference data

Table 1. Quick reference data

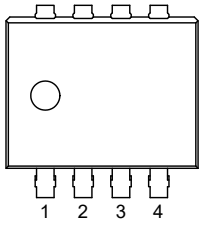
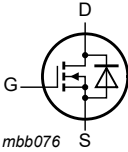
| Symbol                         | Parameter                        | Conditions                                                                                                                 |     | Min | Typ  | Max | Unit |
|--------------------------------|----------------------------------|----------------------------------------------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                 |     | -   | -    | 40  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                  | [1] | -   | -    | 25  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                           |     | -   | -    | 38  | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                            |     |     |      |     |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                              |     | 11  | 15.8 | 20  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                            |     |     |      |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 10\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 1    | 2   | nC   |
| <b>Source-drain diode</b>      |                                  |                                                                                                                            |     |     |      |     |      |
| $Q_r$                          | recovered charge                 | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$               |     | -   | 10   | -   | nC   |

| Symbol | Parameter       | Conditions                                                                                                                             | Min | Typ  | Max | Unit |
|--------|-----------------|----------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| S      | softness factor | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 17</a> | -   | 0.57 | -   |      |

[1] 25A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                         | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p>LFPAK33 (SOT1210)</p> |  |
| 2   | S      | source                            |                                                                                                            |                                                                                     |
| 3   | S      | source                            |                                                                                                            |                                                                                     |
| 4   | G      | gate                              |                                                                                                            |                                                                                     |
| mb  | D      | Mounting base; connected to drain |                                                                                                            |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |                                                                                 |         |
|-------------|---------|---------------------------------------------------------------------------------|---------|
|             | Name    | Description                                                                     | Version |
| BUK9M20-40H | LFPAK33 | Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch | SOT1210 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9M20-40H | 92040H       |

## 8. Limiting values

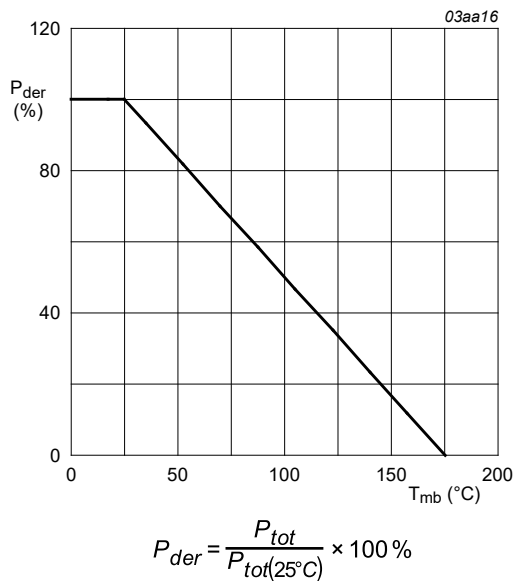
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

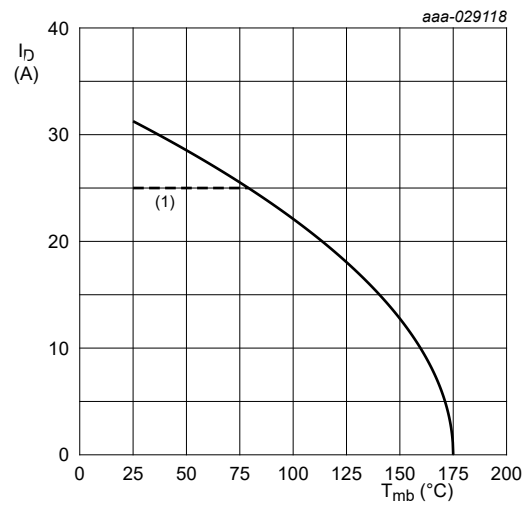
| Symbol             | Parameter               | Conditions                                                                                  | Min | Max | Unit |
|--------------------|-------------------------|---------------------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$           | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                  | -   | 40  | V    |
| $V_{GS}$           | gate-source voltage     | DC; $T_j \leq 175\text{ °C}$                                                                | -10 | 16  | V    |
| $P_{tot}$          | total power dissipation | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                            | -   | 38  | W    |
| $I_D$              | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                   | [1] | 25  | A    |
|                    |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>                  | -   | 22  | A    |
| $I_{DM}$           | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a> | -   | 125 | A    |
| $T_{stg}$          | storage temperature     |                                                                                             | -55 | 175 | °C   |
| $T_j$              | junction temperature    |                                                                                             | -55 | 175 | °C   |
| Source-drain diode |                         |                                                                                             |     |     |      |

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                        |         | Min | Max | Unit |
|-----------------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|-----|------|
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                                           |         | -   | 25  | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                                |         | -   | 125 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                   |         |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 25\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; unclamped; Fig. 4 | [2] [3] | -   | 6.8 | mJ   |

- [1] 25A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.  
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
 [3] Refer to application note AN10273 for further information.



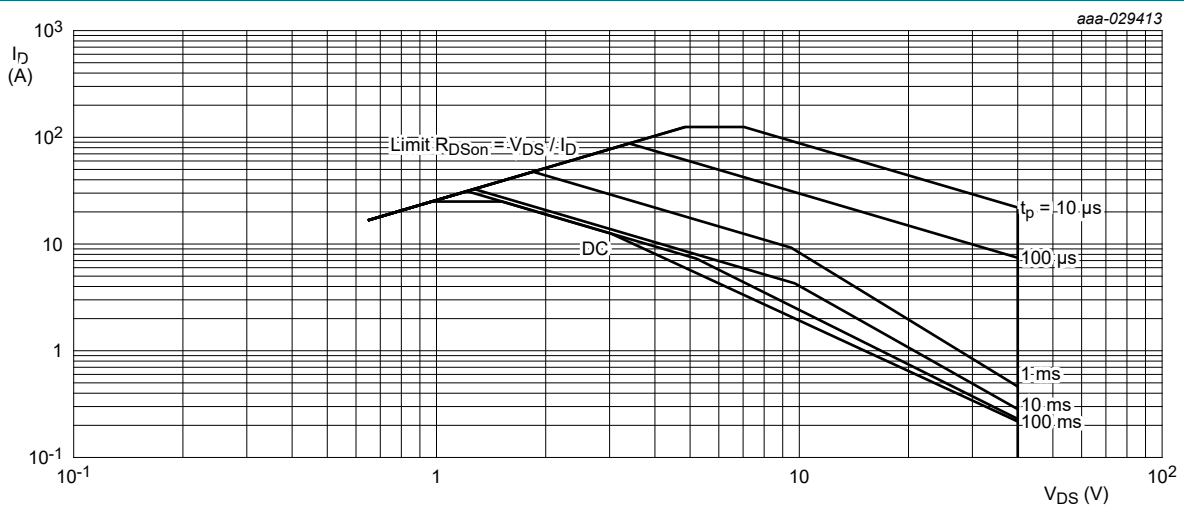
**Fig. 1.** Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

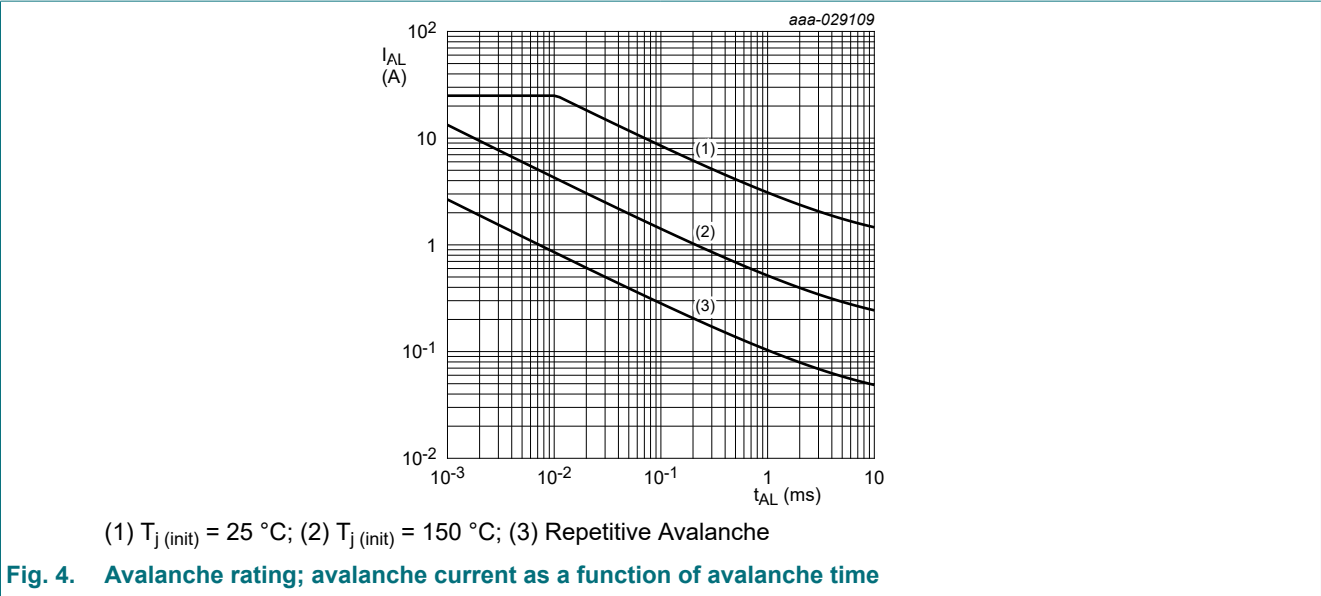
(1) 25A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2.** Continuous drain current as a function of mounting base temperature



$T_{mb} = 25\text{ °C}$ ;  $I_{DM}$  is a single pulse

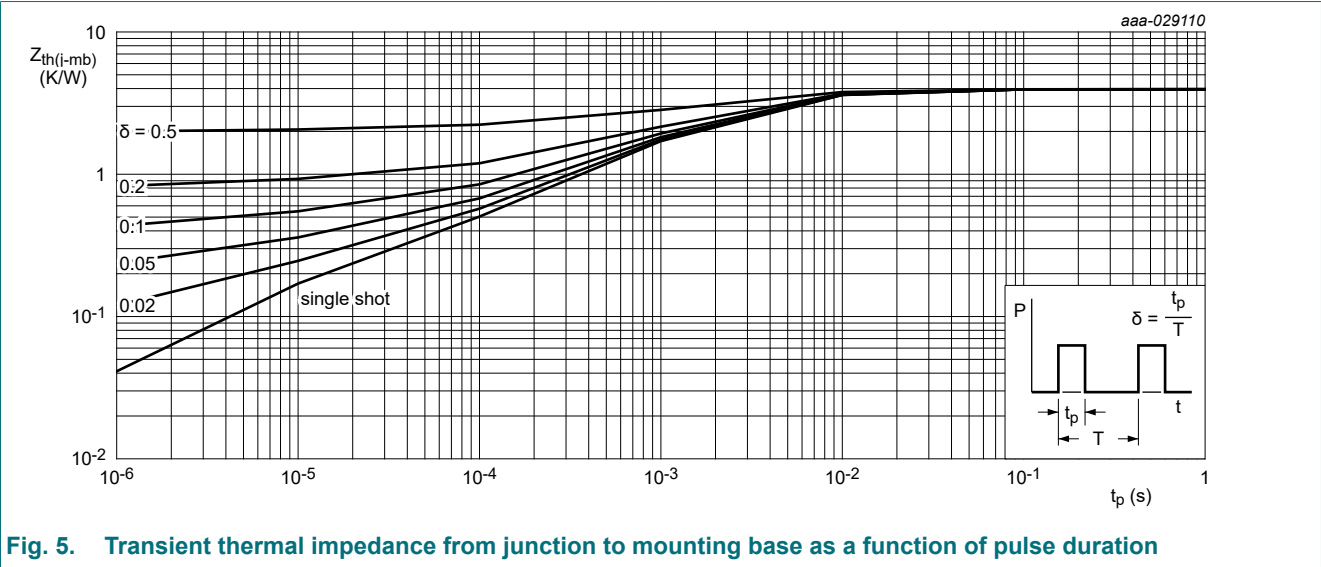
**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | 3.76 | 3.96 | K/W  |



10. Characteristics

Table 7. Characteristics

| Symbol                        | Parameter                      | Conditions                                                                     | Min | Typ  | Max | Unit |
|-------------------------------|--------------------------------|--------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Static characteristics</b> |                                |                                                                                |     |      |     |      |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$  | 40  | 43   | -   | V    |
|                               |                                | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -40\text{ °C}$ | -   | 40.5 | -   | V    |

| Symbol                  | Parameter                        | Conditions                                                                                             |  | Min  | Typ  | Max  | Unit       |
|-------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------|--|------|------|------|------------|
|                         |                                  | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = -55^\circ C$                                               |  | 36   | 40   | -    | V          |
| $V_{GS(th)}$            | gate-source threshold voltage    | $I_D = 1 mA$ ; $V_{DS}=V_{GS}$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a> |  | 1.5  | 1.85 | 2.2  | V          |
|                         |                                  | $I_D = 1 mA$ ; $V_{DS}=V_{GS}$ ; $T_j = -55^\circ C$ ; <a href="#">Fig. 10</a>                         |  | -    | -    | 2.6  | V          |
|                         |                                  | $I_D = 1 mA$ ; $V_{DS}=V_{GS}$ ; $T_j = 175^\circ C$ ; <a href="#">Fig. 10</a>                         |  | 0.7  | -    | -    | V          |
| $I_{DSS}$               | drain leakage current            | $V_{DS} = 40 V$ ; $V_{GS} = 0 V$ ; $T_j = 25^\circ C$                                                  |  | -    | 0.01 | 5    | $\mu A$    |
|                         |                                  | $V_{DS} = 16 V$ ; $V_{GS} = 0 V$ ; $T_j = 125^\circ C$                                                 |  | -    | 0.18 | 10   | $\mu A$    |
|                         |                                  | $V_{DS} = 40 V$ ; $V_{GS} = 0 V$ ; $T_j = 175^\circ C$                                                 |  | -    | 15   | 500  | $\mu A$    |
| $I_{GSS}$               | gate leakage current             | $V_{GS} = 16 V$ ; $V_{DS} = 0 V$ ; $T_j = 25^\circ C$                                                  |  | -    | 2    | 100  | nA         |
|                         |                                  | $V_{GS} = -10 V$ ; $V_{DS} = 0 V$ ; $T_j = 25^\circ C$                                                 |  | -    | 2    | 100  | nA         |
| $R_{DSon}$              | drain-source on-state resistance | $V_{GS} = 10 V$ ; $I_D = 10 A$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 11</a>                          |  | 11   | 15.8 | 20   | m $\Omega$ |
|                         |                                  | $V_{GS} = 10 V$ ; $I_D = 10 A$ ; $T_j = 105^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 15   | 23.1 | 30   | m $\Omega$ |
|                         |                                  | $V_{GS} = 10 V$ ; $I_D = 10 A$ ; $T_j = 125^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 16.6 | 25.1 | 32.2 | m $\Omega$ |
|                         |                                  | $V_{GS} = 10 V$ ; $I_D = 10 A$ ; $T_j = 175^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 20.1 | 30.3 | 38.8 | m $\Omega$ |
|                         |                                  | $V_{GS} = 4.5 V$ ; $I_D = 5 A$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 11</a>                          |  | 13.7 | 19.7 | 25   | m $\Omega$ |
|                         |                                  | $V_{GS} = 4.5 V$ ; $I_D = 5 A$ ; $T_j = 105^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 18.7 | 28.4 | 37.5 | m $\Omega$ |
|                         |                                  | $V_{GS} = 4.5 V$ ; $I_D = 5 A$ ; $T_j = 125^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 20.7 | 30.7 | 40.3 | m $\Omega$ |
|                         |                                  | $V_{GS} = 4.5 V$ ; $I_D = 5 A$ ; $T_j = 175^\circ C$ ; <a href="#">Fig. 12</a>                         |  | 25   | 36.7 | 48.5 | m $\Omega$ |
| $R_G$                   | gate resistance                  | $f = 1 MHz$ ; $T_j = 25^\circ C$                                                                       |  | 0.3  | 0.8  | 2    | $\Omega$   |
| Dynamic characteristics |                                  |                                                                                                        |  |      |      |      |            |
| $Q_{G(tot)}$            | total gate charge                | $I_D = 10 A$ ; $V_{DS} = 20 V$ ; $V_{GS} = 10 V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>   |  | -    | 9    | 12.6 | nC         |
|                         |                                  | $I_D = 10 A$ ; $V_{DS} = 20 V$ ; $V_{GS} = 4.5 V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>  |  | -    | 4.1  | 5.7  | nC         |
| $Q_{GS}$                | gate-source charge               |                                                                                                        |  | -    | 1.8  | 2.7  | nC         |
| $Q_{GD}$                | gate-drain charge                |                                                                                                        |  | -    | 1    | 2    | nC         |
| $C_{iss}$               | input capacitance                | $V_{DS} = 25 V$ ; $V_{GS} = 0 V$ ; $f = 1 MHz$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 15</a>          |  | -    | 545  | 763  | pF         |
| $C_{oss}$               | output capacitance               |                                                                                                        |  | -    | 212  | 297  | pF         |
| $C_{rss}$               | reverse transfer capacitance     |                                                                                                        |  | -    | 22   | 48   | pF         |
| $t_{d(on)}$             | turn-on delay time               | $V_{DS} = 20 V$ ; $R_L = 2 \Omega$ ; $V_{GS} = 4.5 V$ ; $R_{G(ext)} = 5 \Omega$                        |  | -    | 6.2  | -    | ns         |
| $t_r$                   | rise time                        |                                                                                                        |  | -    | 5    | -    | ns         |
| $t_{d(off)}$            | turn-off delay time              |                                                                                                        |  | -    | 6.7  | -    | ns         |
| $t_f$                   | fall time                        |                                                                                                        |  | -    | 3.8  | -    | ns         |
| Source-drain diode      |                                  |                                                                                                        |  |      |      |      |            |
| $V_{SD}$                | source-drain voltage             | $I_S = 10 A$ ; $V_{GS} = 0 V$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 16</a>                           |  | -    | 0.86 | 1.2  | V          |
| $t_{rr}$                | reverse recovery time            | $I_S = 10 A$ ; $dI_S/dt = -100 A/\mu s$ ; $V_{GS} = 0 V$ ; $V_{DS} = 20 V$ ; <a href="#">Fig. 17</a>   |  | -    | 18   | -    | ns         |
| $Q_r$                   | recovered charge                 | $I_S = 10 A$ ; $dI_S/dt = -100 A/\mu s$ ; $V_{GS} = 0 V$ ; $V_{DS} = 20 V$                             |  | -    | 10   | -    | nC         |

| Symbol | Parameter       | Conditions                                                                                                                             |  | Min | Typ  | Max | Unit |
|--------|-----------------|----------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| S      | softness factor | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 17</a> |  | -   | 0.57 | -   |      |
|        |                 | $I_S = 10\text{ A}$ ; $dI_S/dt = -500\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 17</a> |  | -   | 0.34 | -   |      |

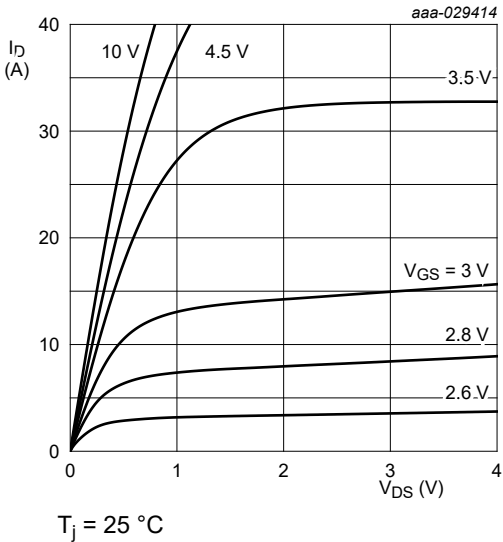


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

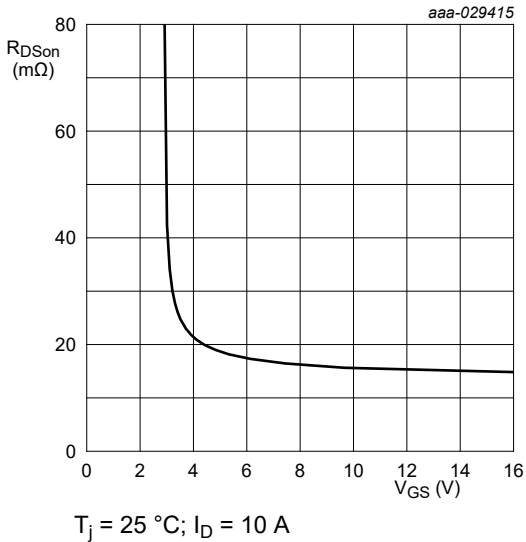


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

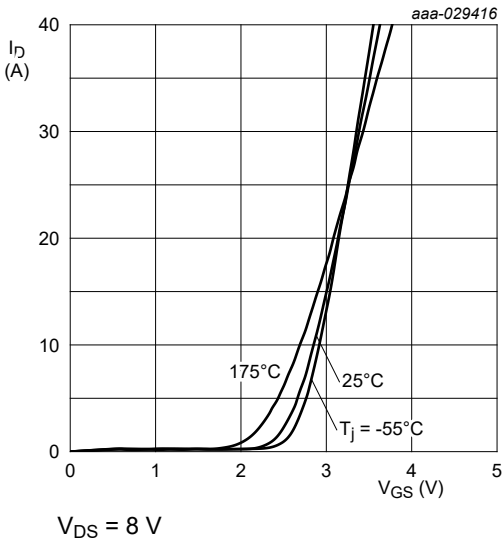


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

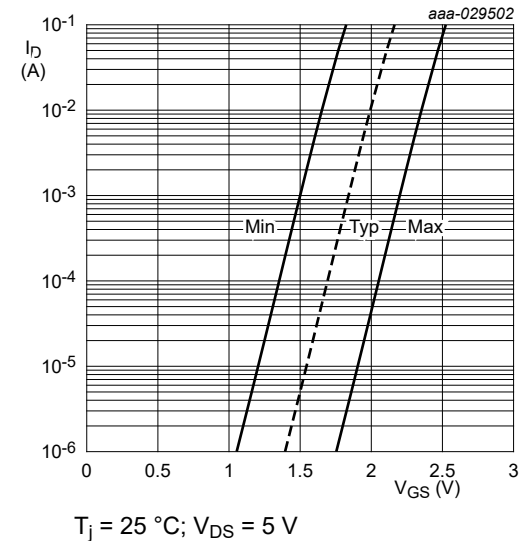


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

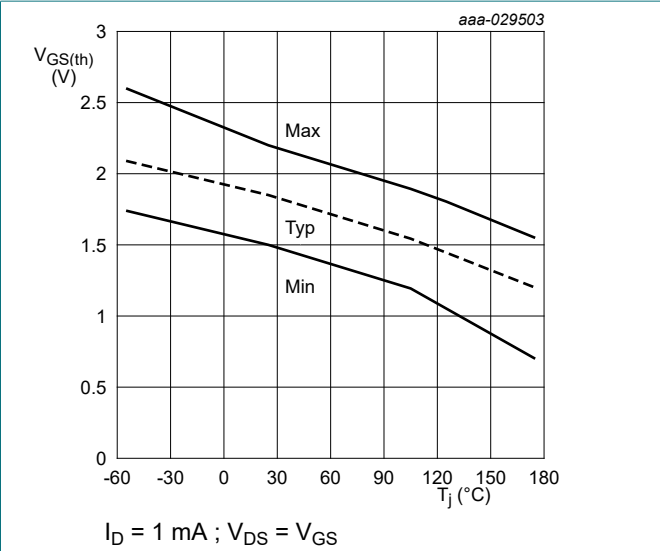


Fig. 10. Gate-source threshold voltage as a function of junction temperature

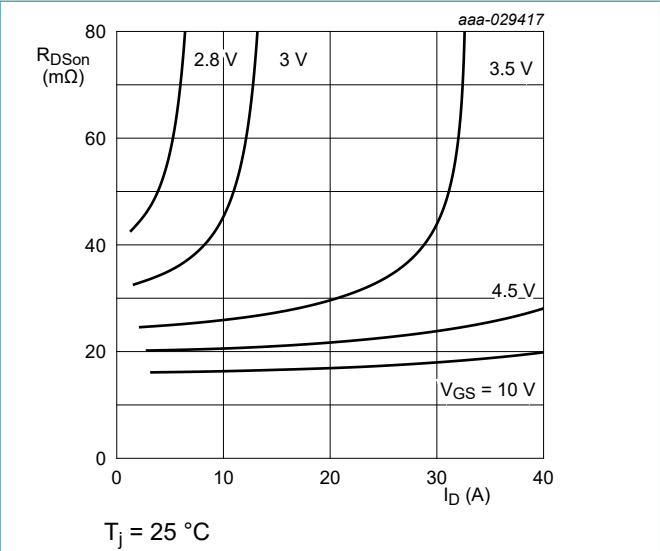


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

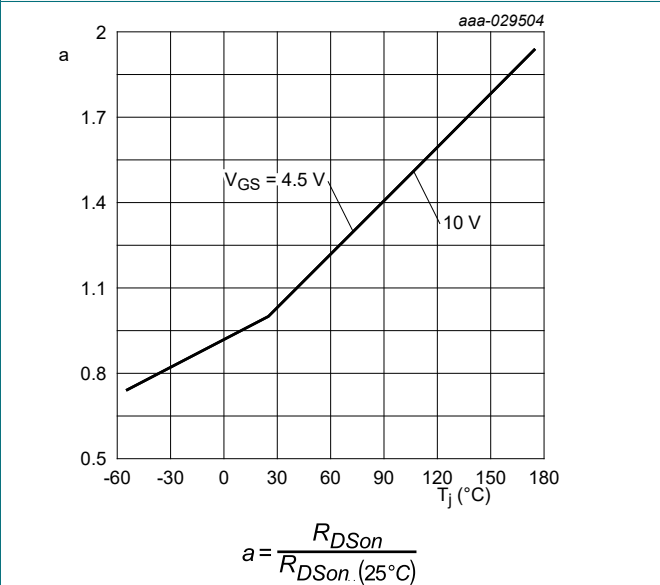


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

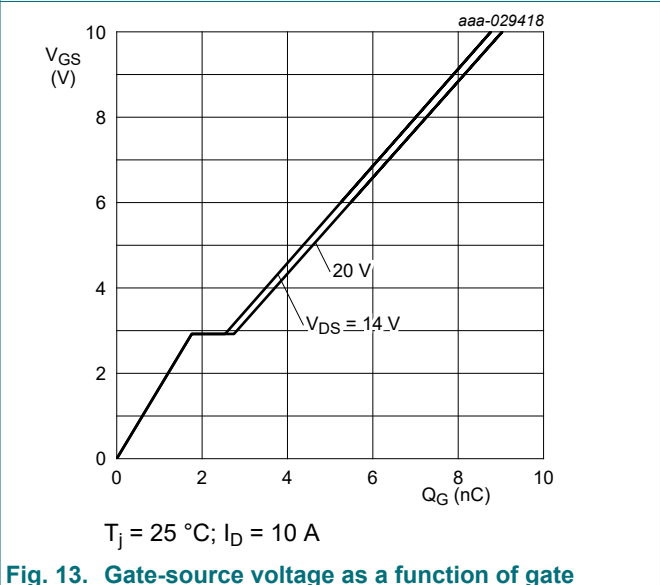


Fig. 13. Gate-source voltage as a function of gate charge; typical values

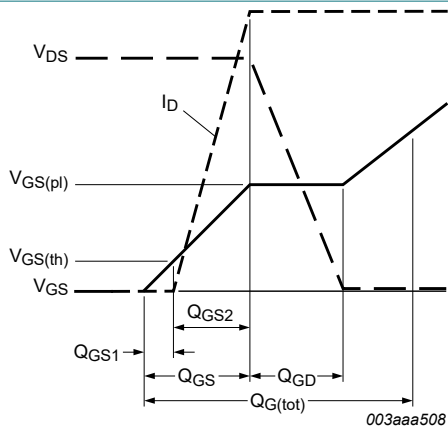
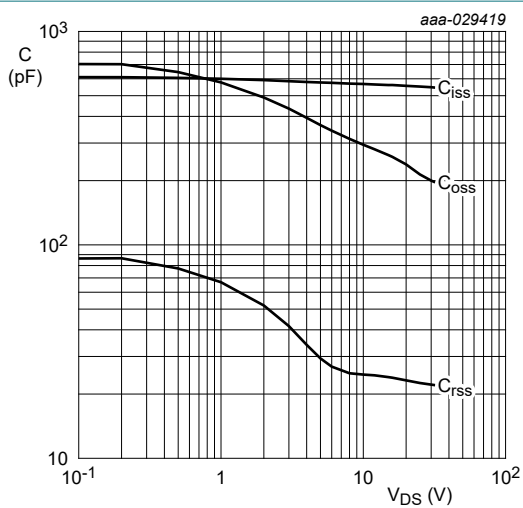
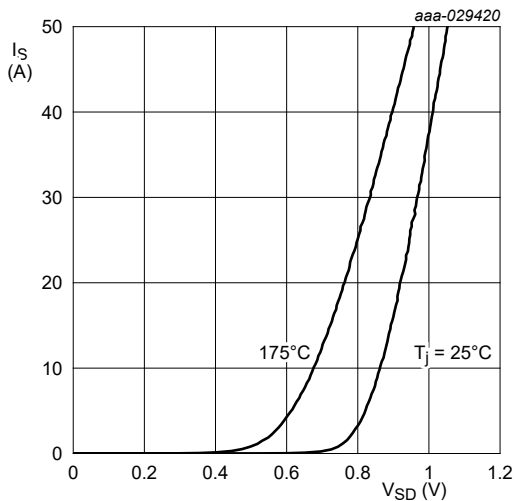


Fig. 14. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

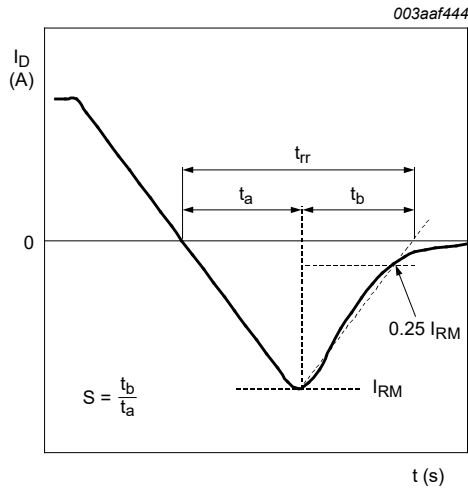


Fig. 17. Reverse recovery timing definition

11. Package outline

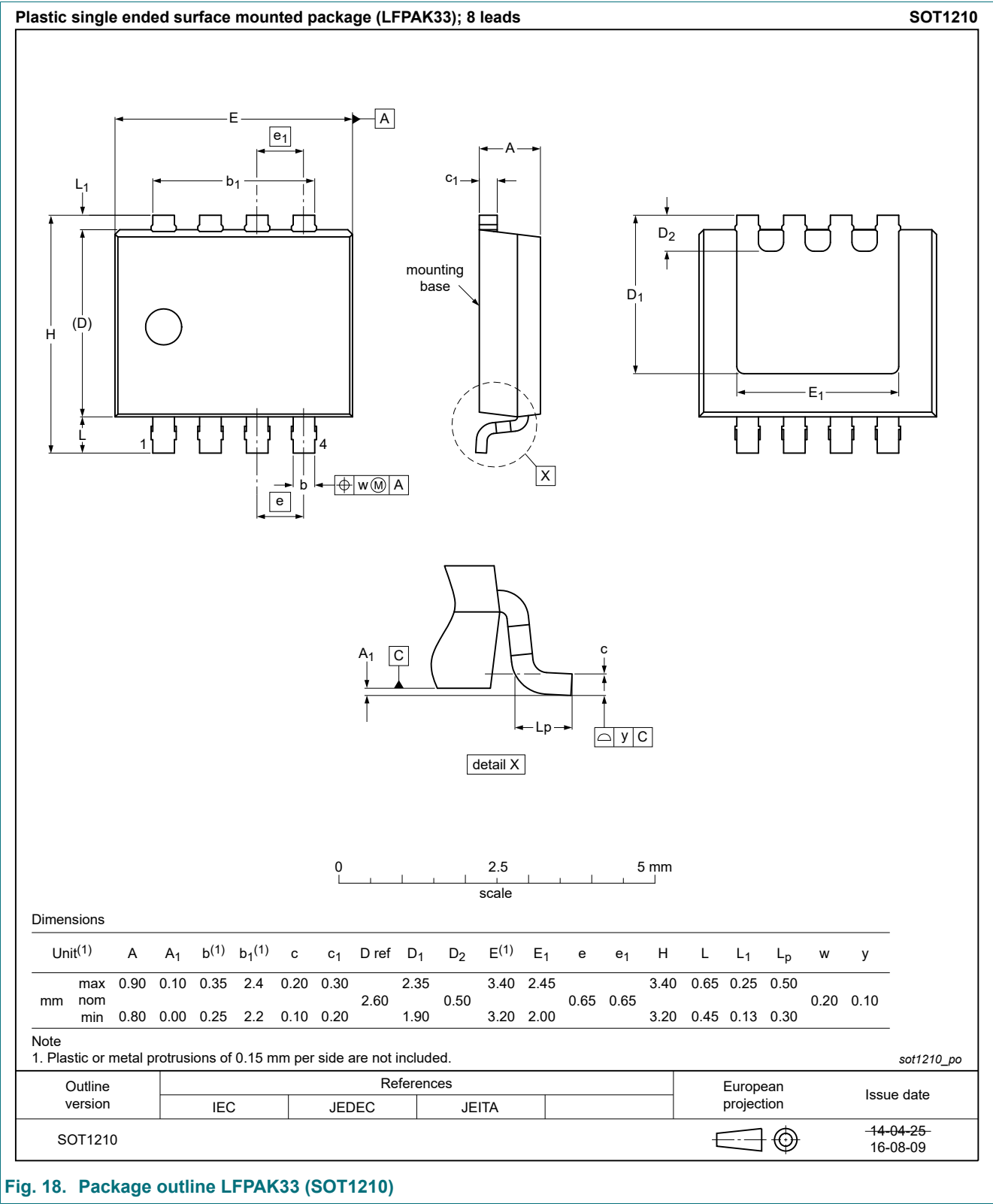


Fig. 18. Package outline LPAK33 (SOT1210)

## 12. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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Contents

1. General description..... 1

2. Features and benefits..... 1

3. Applications..... 1

4. Quick reference data..... 1

5. Pinning information.....2

6. Ordering information.....2

7. Marking.....2

8. Limiting values..... 2

9. Thermal characteristics..... 4

10. Characteristics..... 4

11. Package outline..... 9

12. Legal information.....10

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